

1-Line Bi-directional TVS Diode

Description

The PESDU2881D3 is a 2.8V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The PESDU2881D3 complies with the IEC 61000-4-2 (ESD) with ± 30 kV air and ± 30 kV contact discharge. It is assembled into a SOD-323 leadfree package. The small size and high ESD surge protection make PESDU2881D3 an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

Features

- Protects one data or power line
- Ultra low leakage: μA level
- Operating voltage: 2.8V
- Low clamping voltage
- 2-Pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: ± 30 kV
 - Contact discharge: ± 30 kV
 - IEC 61000-4-5 (Lightning) 150A (8/20 μs)
- RoHS Compliant

Mechanical Characteristics

- Package: SOD-323
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Marking Information: See Below

Applications

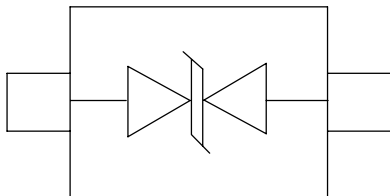
- Cellular Handsets and Accessories
- Personal Digital Assistants
- Notebooks and Handhelds
- Portable Instrumentation
- Digital Cameras
- Peripherals
- Audio Players

Marking Information



28D = Device Marking Code

Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Shipping	Reel Size
PESDU2881D3	3,000/Tape & Reel	7 inch

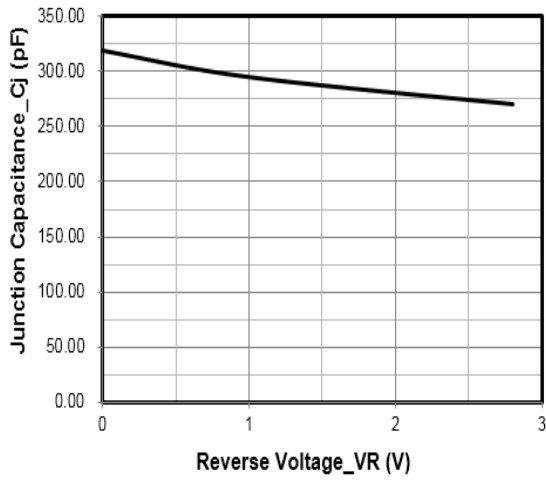
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P _{pk}	3000	W
Peak Pulse Current (8/20 μs)	I _{pp}	150	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±30 ±30	kV
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

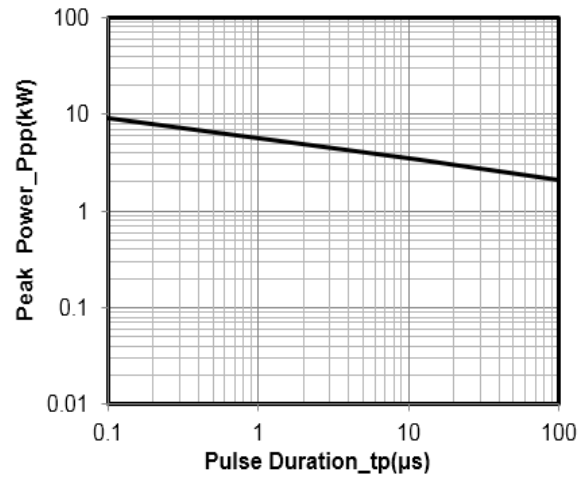
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			2.8	V	
Breakdown Voltage	V _{BR}	3.0	3.75		V	I _T = 1mA
Reverse Leakage Current	I _R			1	μA	V _{RWM} = 2.8V
Clamping Voltage	V _C		18	20	V	I _{PP} = 150A (8 x 20μs pulse)
Junction Capacitance	C _J		320		pF	V _R = 0V, f = 1MHz

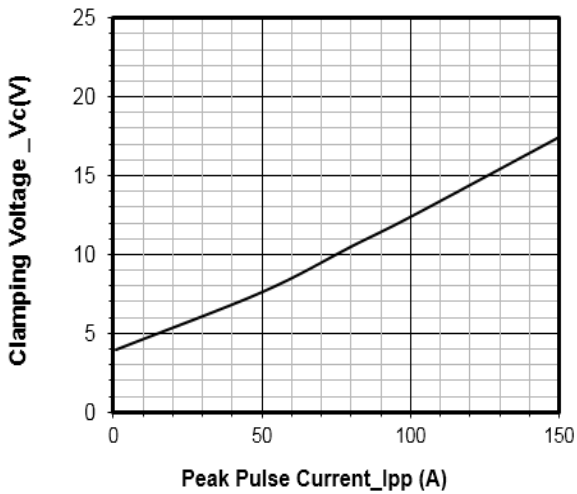
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



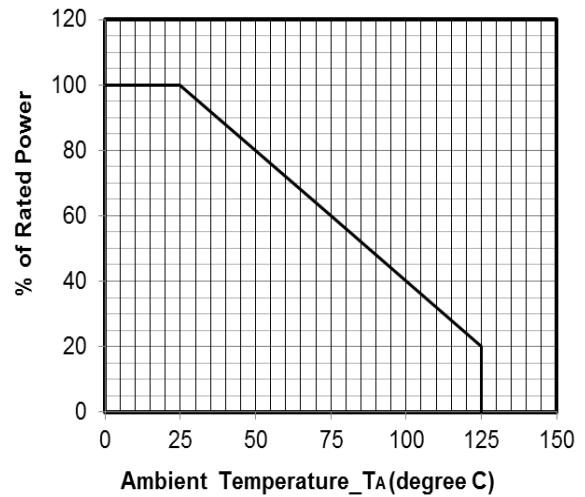
Junction Capacitance vs. Reverse Voltage



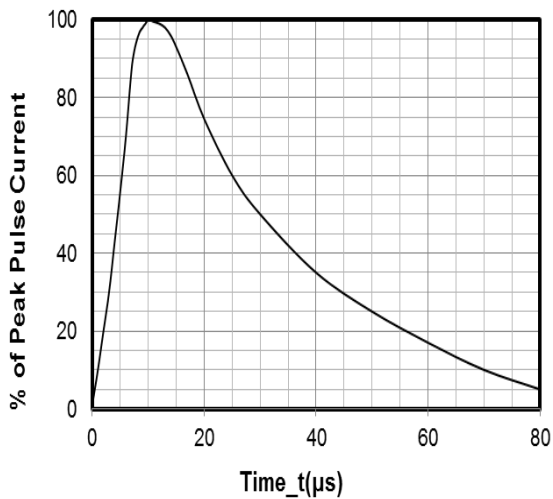
Peak Pulse Power vs. Pulse Time



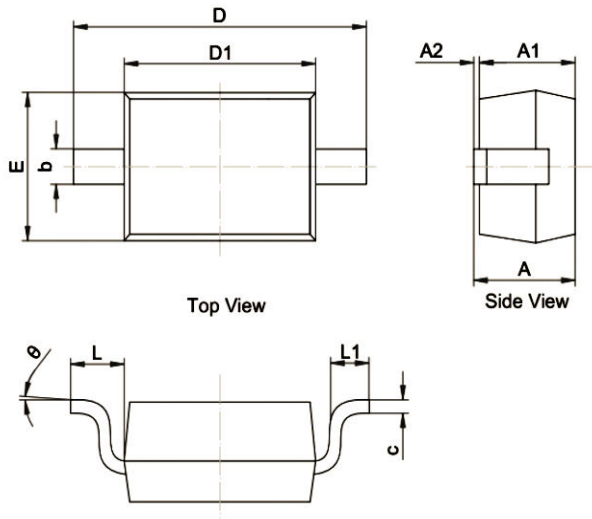
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



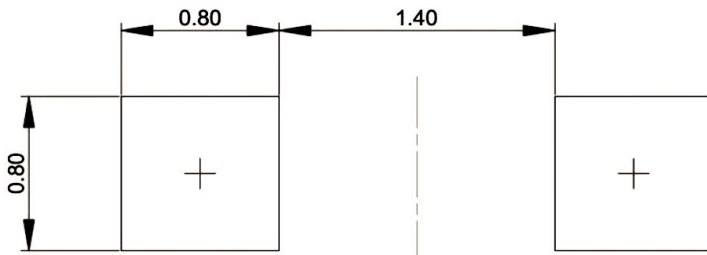
8/20μs Pulse Waveform



SYM	MILLIMETERS		
	MIN	NOM	MAX
A	0.800	--	1.100
A1	0.800	--	0.900
A2	0.000	--	0.100
b	0.250	--	0.400
c	0.080	--	0.177
D1	1.600	1.700	1.800
D	2.300	--	2.800
E	1.150	--	1.400
L	0.475REF		
L1	0.100	--	0.500
Θ	0°	--	8°

Suggested Land Pattern

Unit: mm



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [ESD Suppressors / TVS Diodes](#) category:

Click to view products by [PN SILICON](#) manufacturer:

Other Similar products are found below :

[NTE4902](#) [P4SMAJ15A](#) [P4SMAJ26A](#) [SMAJ400CA-TP](#) [TGL34-47CA](#) [ESDAULC45-1BF4](#) [SM1605E3/TR13](#) [SMF20A-TP](#) [P4SMAJ12A](#)
[CPDUR24V-HF](#) [CPDQC5V0USP-HF](#) [CPDQC5V0-HF](#) [MPLAD30KP45CAE3](#) [MMBZ27VCLQ-7-F](#) [MMAD1108/TR13](#) [MPLAD30KP24A](#)
[ACPDQC5V0R-HF](#) [DFLT170A-7](#) [NTE4900](#) [NTE4926](#) [NTE4938](#) [SMF22A-TP](#) [SMF12A-TP](#) [SLVU2.8-TP](#) [SMLJ6.5CA-TP](#) [SMAJ6.5CA-](#)
[TP](#) [MMAD1108E3/TR13](#) [D5V0M1U2LP3-7](#) [SMAJ400A-TP](#) [AOZ8811DT-03](#) [AOZ8831DI-05](#) [AOZ8831DT-03](#) [SMAJ188CA](#) [3SMC33CA](#)
[BK](#) [CPDQC3V3C-HF](#) [CPDQC12VE-HF](#) [MPLAD30KP170CA](#) [82357120100](#) [5.0SMLJ15CA-TP](#) [5KP18A-TP](#) [P6KE8.2A-TP](#)
[MPLAD30KP43CAE3](#) [SMAJ43A-TP](#) [D5V0F6U8LP33-7](#) [TVS5501V10MUT5G](#) [5.0SMLJ24CA-TP](#) [SMAJ110CA-TP](#) [MPLAD15KP75CAE3](#)
[MMAD1103e3/TR13](#) [DFLT40AQ-7](#)